

TOSHIBA Diode Silicon Epitaxial Planar Type

JDV3C11

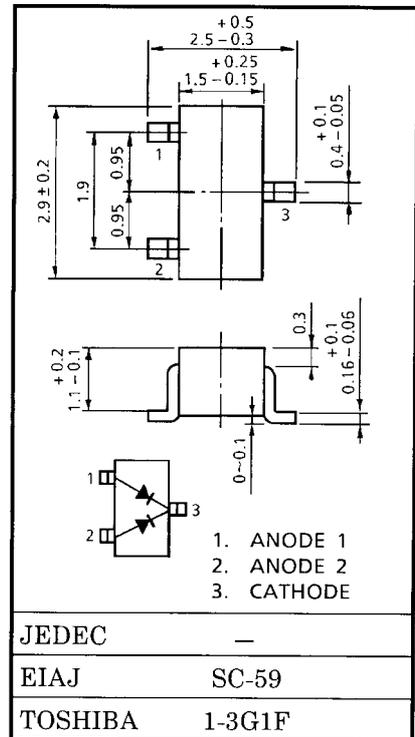
Electronic Tuning Applications of FM Receivers

- High capacitance ratio: $C_{1V}/C_{4.5V} = 5.3$ (typ.)
- Low series resistance: $r_s = 0.4 \Omega$ (typ.)
- Two diodes in a single package

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Reverse voltage	V_R	20	V
Junction temperature	T_j	125	°C
Storage temperature range	T_{stg}	-55~125	°C

Unit in mm



Weight : 0.013g

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Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Reverse voltage	V_R	$I_R = 1 \mu\text{A}$	20	—	—	V
Reverse current	I_R	$V_R = 20 \text{ V}$	—	—	10	nA
Capacitance	C_{1V}	$V_R = 1 \text{ V}, f = 1 \text{ MHz}$	65.8	—	74.2	pF
	$C_{4.5V}$	$V_R = 4.5 \text{ V}, f = 1 \text{ MHz}$	11.5	—	14.3	
Capacitance ratio	$C_{1V}/C_{4.5V}$	—	5	5.3	—	—
Series resistance	r_s	$V_R = 1.5 \text{ V}, f = 100 \text{ MHz}$	—	0.4	0.6	Ω

Note 1: Signal level when capacitance is measured. $V_{\text{sig}} = 20 \text{ mVrms}$

Note 2: Electrical characteristics shown in the above are between anode 1 and cathode, between anode 2 and cathode.

Marking

